

Amendments to the Specification:

Please amend the title as follows:

**MAGNETORESISTIVE HEAD WITH A MAGNETIC DOMAIN CONTROL
UNDERLAYER BELOW A MAGNETORESISTIVE FILM AND MANUFACTURING
METHOD THEREOF**

Please amend paragraph [0028] as follows:

[0028] The following table includes a description of reference numerals, and is a useful legend for the different layers shown in various ones of the figures.

Table 1

1	underlayer
2	free layer
3	non-magnetic layer
4	pinned layer
5	anti-ferromagnetic layer
6	cap layer
7	lower magnetic shield
8	lower dielectric gap layer
8a	lower dielectric gap layer protruded portion
8b	lower dielectric gap layer extended portion
9	magnetic domain control underlayer
10	magnetic domain control film
11	electrode film
12	upper dielectric gap layer
13	upper magnetic shield
14	resist
15	lower magnetic shield
16	dielectric layer
17	magnetoresistive multi-layered film
18	dielectric layer
19	upper magnetic shield
20	dielectric layer
21a	lower magnetic pole
21b	lower magnetic pole protrusion
22a	upper magnetic pole 1
22b	upper magnetic pole
23	coil

24	dielectric layer
L	multi-layered film
M	magnetic domain control stack

Please amend paragraph [0044] as follows:

[0044] The conditions for forming Sample Nos. 1 - 5 are as shown in Table 2 [[1]]. Sample No. 1 is an existing example constituted only with a multi-layered film with no magnetic domain control underlayer, which is referred to hereinafter as a standard sample. Sample Nos. 2 to 4 are constituted with a magnetic domain control underlayer and a multi-layered film. The magnetic domain control underlayer was formed by using Cr to a thickness of 10 nm. Further, as the pretreatment for the underlayer deposition, a treatment comprising only atmospheric exposure (exposure in atmosphere for 5 min) or plasma oxidation (in pure oxygen gas, at a gas pressure 0.9 Pa, RF power of 15 W, for 60 sec of time) after atmospheric exposure was applied.

Please amend paragraph [0045] as follows:

[0045] Table 2 [[1]]

Sample No.	Magnetic domain control underlayer	Pretreatment for underlayer deposition	Underlayer
1	-	Atmospheric exposure	Underlayer A
2	Cr 10 nm	Atmospheric exposure	Underlayer A
3	Cr 10 nm	Atmospheric exposure	Ta 1 nm Atmospheric exposure underlayer A
4	Cr 10 nm	Atmospheric exposure plasma oxidation	Underlayer A
5	Cr 10 nm	Atmospheric exposure plasma oxidation	Ta 1 nm Atmospheric exposure underlayer A